



## Absolute Maximum Ratings:

Collector-Emitter Voltage, $V_{CE0}$	: 50V
Collector-Base Voltage, $V_{CB0}$	: 75V
Emitter-Base Voltage, $V_{EB0}$	: 5V
Continuous Collector Current, $I_C$	: 2A
Base Current, $I_B$	: 1A
Total Power Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_D$	: 10W
Derate Above $25^\circ\text{C}$	: 0.057W/ $^\circ\text{C}$
Operating Junction Temperature, $T_J$	: $-65^\circ\text{C}$ to $200^\circ\text{C}$
Storage Temperature Range, $T_{stg}$	: $-65^\circ\text{C}$ to $200^\circ\text{C}$
Thermal Resistance, Junction -to-Case, $R_{thJC}$	: $17.5^\circ\text{C/W}$

## Electrical Characteristics: ( $T_A = +25^\circ\text{C}$ Unless otherwise specified):

Parameter	Symbol	Test Conditions	Min	Max	Unit
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### OFF Characteristics

Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\text{mA}$ , $I_B = 0$ (Note1)	50	-	V
Collector Cutoff Current	$I_{CEX}$	$V_{CE} = 75\text{V}$ , $V_{BE} = 1.5\text{V}$	-	0.1	mA
		$V_{CE} = 45\text{V}$ , $V_{BE} = 1.5\text{V}$ , $T_C = +150^\circ\text{C}$	-	5	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{BE} = 5\text{V}$ , $I_C = 0$	-	0.1	mA

### ON Characteristics (Note 1)

DC Current Gain	$h_{FE}$	$I_C = 500\text{mA}$ , $V_{CE} = 4\text{V}$	40	250	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}$ , $I_B = 50\text{mA}$	-	1.2	V
Base-Emitter ON Voltage	$V_{BE(on)}$	$I_C = 500\text{mA}$ , $V_{CE} = 4\text{V}$	-	1.4	V

### Small-Signal Characteristics

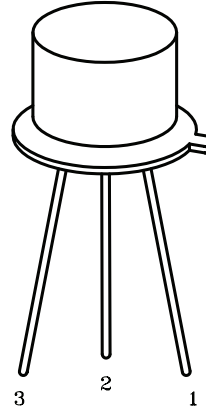
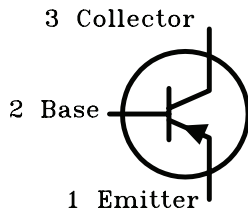
Small-Signal Current Gain	$h_{fe}$	$I_C = 50\text{mA}$ , $V_{CE} = 4\text{V}$ , $f = 10\text{MHz}$	5.0	-	-
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### Switching Characteristics

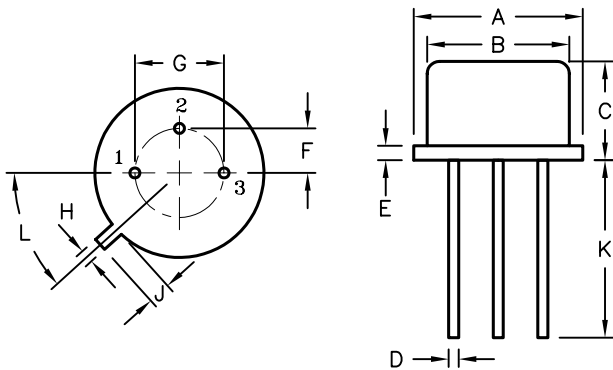
Turn-On Time	$t_{on}$	$V_{CC} = 30\text{V}$ , $I_C = 500\text{mA}$ , $I_{B1} = 50\text{mA}$	-	100	ns
Turn-Off Time	$t_{off}$	$V_{CC} = 30\text{V}$ , $I_C = 500\text{mA}$ , $I_{B2} = 50\text{mA}$	-	1,000	ns

Notes: 1. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

## PNP



- 1. EMITTER
- 2. BASE
- 3. Collector



Dimensions	A	B	C	D	E	F	G	H	J	K	L
Min.	8.5	7.74	6.09	0.4	-	2.41	4.82	0.71	0.73	12.7	45°
Max.	9.39	8.5	6.6	0.53	0.88	2.66	5.33	0.86	1.02	-	48°

Dimensions : Millimetres

### Part Number Table

Description	Part Number
Transistor, Silicon, TO-39, PNP, General Purpose	2N5323

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